

Vishay Siliconix

Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)			
- 20	0.051 at V _{GS} = - 4.5 V	- 5.7			
	0.067 at V _{GS} = - 2.5 V	- 5.0			
	0.094 at V _{GS} = - 1.8 V	- 4.2			

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFETS: 1.8 V Rated
- New Low Thermal Resistance PowerPAK® • Package

APPLICATIONS

- Portable
 - PA Switch
 - Battery Switch
 - Load Switch





P-Channel MOSFET

P-Channel MOSFET

Ordering Information: Si7911DN-T1-E3 (Lead (Pb)-free)						
Si7911DN-T1-GE3 (Lead (Pb)-free and	Halogen-free)					

ABSOLUTE MAXIMUM RATINGS	Γ _A = 25 °C, ι	unless otherwis	e noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current (T 150 °C)a	T _A = 25 °C	l _D	- 5.7	- 4.2	٨	
Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$	T _A = 85 °C		- 4.1	- 3.0		
Pulsed Drain Current		I _{DM}	- 20		A	
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.1	- 1.1		
Mariana David Disaination	T _A = 25 °C	– P _D	2.5	1.3	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.3	0.85	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations ^{b, c}			260		C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manimum has alien to Assistanta	t ≤ 10 s	- R _{thJA}	40	50		
Maximum Junction-to-Ambient ^a	Steady State		75	94	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	5.6	7		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



COMPLIANT

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static			•					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 0.40		- 1.0	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1			
		V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 85 °C			- 5	μA		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 20			А		
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 5.7 A		0.040	0.051	1		
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 5.0 A		0.054	0.067	Ω		
		V _{GS} = - 1.8 V, I _D = - 1.1 A		0.075	0.094			
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -6 V, I_{D} = -5.7 A$		14		S		
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S}$ = - 2.3 A, $V_{\rm GS}$ = 0 V		- 0.8	- 1.2	V		
Dynamic ^b			•	•				
Total Gate Charge	Qg			9.5	15			
Gate-Source Charge	Q _{gs}	V_{DS} = - 6 V, V_{GS} = - 4.5 V, I_{D} = - 5.7 A		1.6		nC		
Gate-Drain Charge	Q _{gd}			2.5				
Gate Resistance	Rg			7.2		Ω		
Turn-On Delay Time	t _{d(on)}			20	30			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		35	55	ns		
Turn-Off DelayTime	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_G = 6 Ω		70	105			
Fall Time	t _f			40	60			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dl/dt = 100 A/μs		25	50			

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $T_A = 25 \text{ °C}$, unless otherwise noted







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Capacitance





On-Resistance vs. Gate-to-Source Voltage

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Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

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